



GL80N60A47P

Silicon N-Channel Power MOSFET

General Description:

GL80N60A47P, the silicon N-channel Enhanced VDMOSFET, is obtained by the self-aligned planar Technology which reduce the conduction loss, improve switching performance and

enhance the avalanche energy. The transistor can be used in various power switching circuit for system miniaturization and higher efficiency. The package form is TO-247PLUS, which accords with the RoHS standard.

Features:

- Fast Switching
- Low Gate Charge (Typical Data: 220nC)
- Low Reverse transfer capacitances(Typical: 160pF)
- 100% Single Pulse avalanche energy Test
-

Applications:

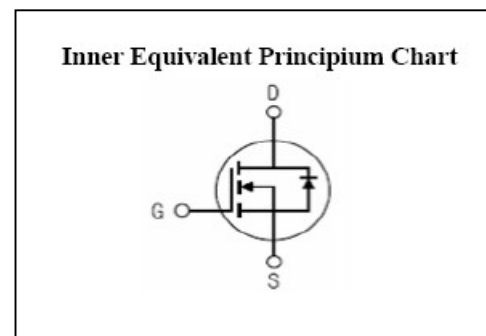
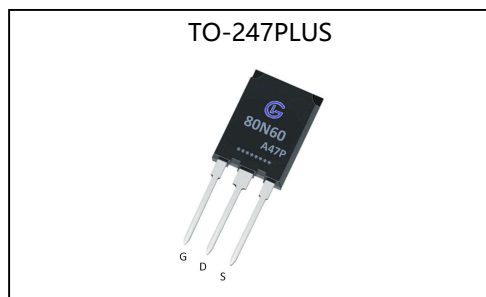
- Power switch circuit of PC POWER

Absolute ($T_c=25^{\circ}\text{C}$ unless otherwise specified):

Symbol	Parameter	Rating	Units
V_{DS}	Drain-to-Source Voltage	600	V
I_D	Continuous Drain Current	80	A
	Continuous Drain Current $T_c=100^{\circ}\text{C}$	56	A
I_{DM}^{a1}	Pulsed Drain Current	240	A
V_{GS}	Gate-to-Source Voltage	± 30	V
E_{AS}	Single Pulse Avalanche Energy	4	J
E_{Ar}^{a1}	Avalanche Energy ,Repetitive	800	mJ
I_{AR}^{a1}	Avalanche Current	120	A
dv/dt^{a2}	Peak Diode Recovery dv/dt	5.0	V/ns
P_D	Power Dissipation	961	W
	Derating Factor above 25°C	7.688	W/ $^{\circ}\text{C}$
T_J, T_{stg}	Operating Junction and Storage Temperature Range	150, -55 to 150	$^{\circ}\text{C}$
T_L	Maximum Temperature for Soldering	300	$^{\circ}\text{C}$

Caution Stresses greater than those in the "Absolute Maximum Ratings" may cause permanent damage to the device

$V_{DS}(T_c=150^{\circ}\text{C})$	600	V
I_D	80	A
$P_D(T_c=25^{\circ}\text{C})$	961	W
$R_{DS(ON)}$	60	m Ω





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Thermal Characteristics

Symbol	Parameter	Rating	Units
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	0.13	$^{\circ}\text{C}/\text{W}$
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	20	$^{\circ}\text{C}/\text{W}$

Electrical Characteristics (Tc= 25 $^{\circ}\text{C}$ unless otherwise specified) :

OFF Characteristics						
Symbol	Parameter	Test Conditions	Rating			Units
			Min.	Typ.	Max.	
V_{DSS}	Drain to Source Breakdown Voltage	$V_{GS}=0\text{V}, I_D=250\mu\text{A}$	600	--	--	V
I_{DSS}	Drain to Source Leakage Current	$V_{DS}=600\text{V}, V_{GS}=0\text{V}, T_a=25^{\circ}\text{C}$	--	--	10	μA
		$V_{DS}=480\text{V}, V_{GS}=0\text{V}, T_a=125^{\circ}\text{C}$	--	--	1000	
$I_{GSS(F)}$	Gate to Source Forward Leakage	$V_{GS}=+20\text{V}$	--	--	200	nA
$I_{GSS(R)}$	Gate to Source Reverse Leakage	$V_{GS}=-20\text{V}$	--	--	-200	nA

ON Characteristics						
Symbol	Parameter	Test Conditions	Rating			Units
			Min.	Typ.	Max.	
$R_{DS(ON)}$	Drain-to-Source On-Resistance	$V_{GS}=10\text{V}, I_D=40\text{A}$	--	60	75	m Ω
$V_{GS(TH)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_D=250\mu\text{A}$	2.0	--	4.0	V
g_{fs}	Forward Trans conductance	$V_{DS}=30\text{V}, I_D=40\text{A}$	--	100	--	S
Pulse width<380 μs ; duty cycle<2%.						

Dynamic Characteristics						
Symbol	Parameter	Test Conditions	Rating			Units
			Min.	Typ.	Max.	
C_{iss}	Input Capacitance	$V_{GS}=0\text{V}, V_{DS}=25\text{V}$ $f=1.0\text{MHz}$	--	13000	--	pF
C_{oss}	Output Capacitance		--	1250	--	
C_{rss}	Reverse Transfer Capacitance		--	160	--	

Resistive Switching Characteristics						
Symbol	Parameter	Test Conditions	Rating			Units
			Min.	Typ.	Max.	
$t_{d(ON)}$	Turn-on Delay Time	$I_D=60\text{A}, V_{DD}=300\text{V}$ $V_{GS}=10\text{V}, R_g=25\Omega$	--	69	--	ns
t_r	Rise Time		--	125	--	
$t_{d(OFF)}$	Turn-Off Delay Time		--	488	--	
t_f	Fall Time		--	150	--	
Q_g	Total Gate Charge	$I_D=60\text{A}, V_{DD}=300\text{V}$ $V_{GS}=10\text{V}$	--	220	--	nC
Q_{gs}	Gate to Source Charge		--	50	--	
Q_{gd}	Gate to Drain ("Miller")Charge		--	80	--	

Source-Drain Diode Characteristics

Symbol	Parameter	Test Conditions	Rating			Units
			Min.	Typ.	Max.	
I_{SD}	Continuous Source Current (Body Diode)		--	--	80	A
I_{SM}	Maximum Pulsed Current (Body Diode)		--	--	240	A
V_{SD}	Diode Forward Voltage	$I_S=80A, V_{GS}=0V$	--	--	1.5	V
t_{rr}	Reverse Recovery Time	$I_S=40A, T_J=25^\circ C$	--	490	--	ns
Q_{rr}	Reverse Recovery Charge	$di_F/dt=100A/\mu s, V_{GS}=0V$	--	4.82	--	uC

a1: Repetitive rating; pulse width limited by maximum junction temperature

a2: $I_{SD}=100A, di/dt \leq 100A/\mu s, V_{DD} \leq BV_{DS}$, Start $T_J=25^\circ C$

Test Circuit and Waveform

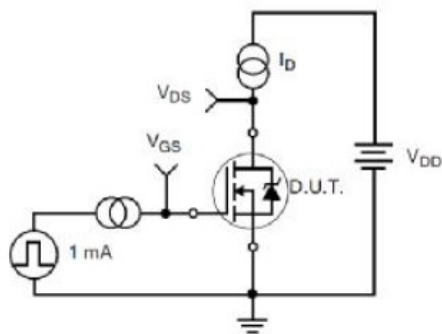


Figure 17. Gate Charge Test Circuit

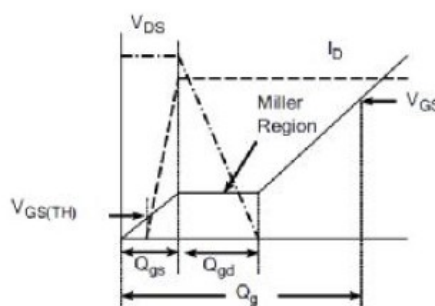


Figure 18. Gate Charge Waveform

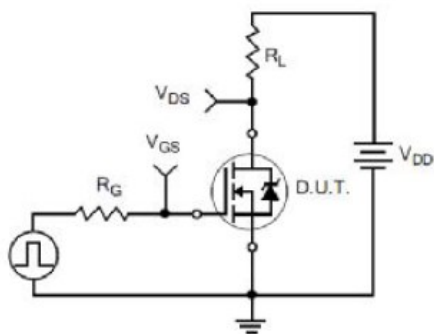


Figure 19. Resistive Switching Test Circuit

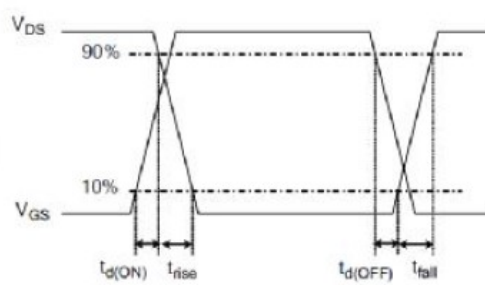


Figure 20. Resistive Switching Waveforms



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Characteristics Curve:

Fig. 1. Output Characteristics @ $T_J = 25^\circ\text{C}$

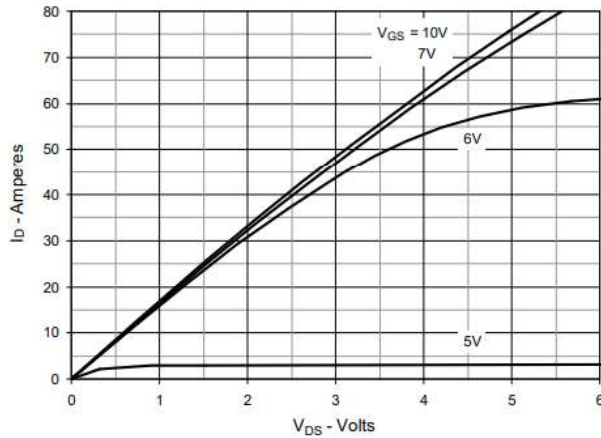


Fig. 2. Extended Output Characteristics @ $T_J = 25^\circ\text{C}$

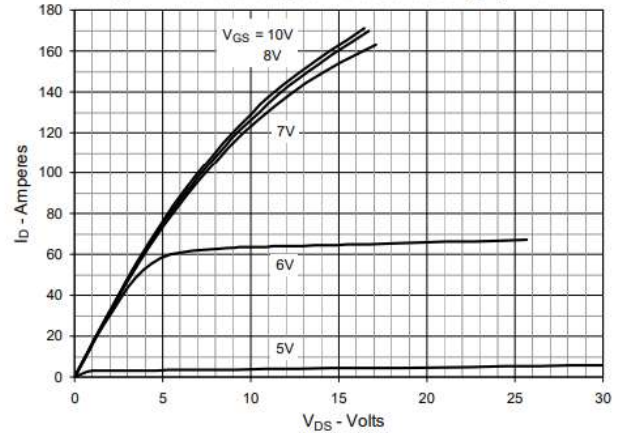


Fig. 3. Output Characteristics @ $T_J = 125^\circ\text{C}$

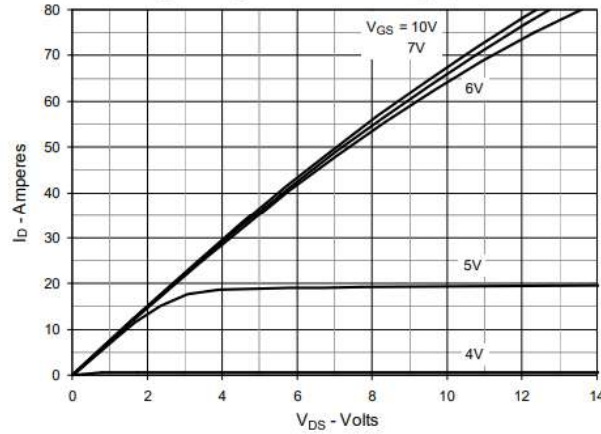


Fig. 4. $R_{DS(on)}$ Normalized to $I_D = 40\text{A}$ Value vs. Junction Temperature

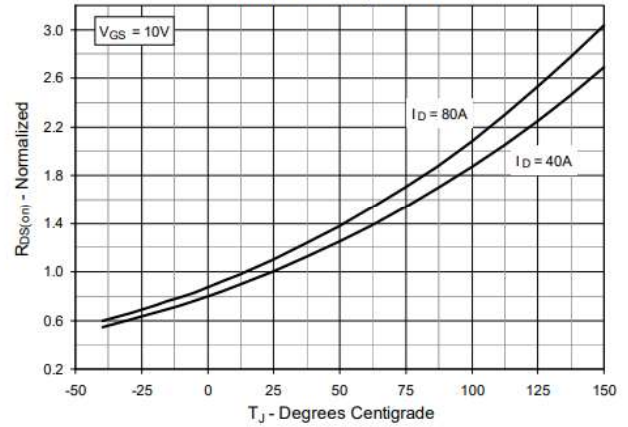


Fig. 5. $R_{DS(on)}$ Normalized to $I_D = 40\text{A}$ Value vs. Drain Current

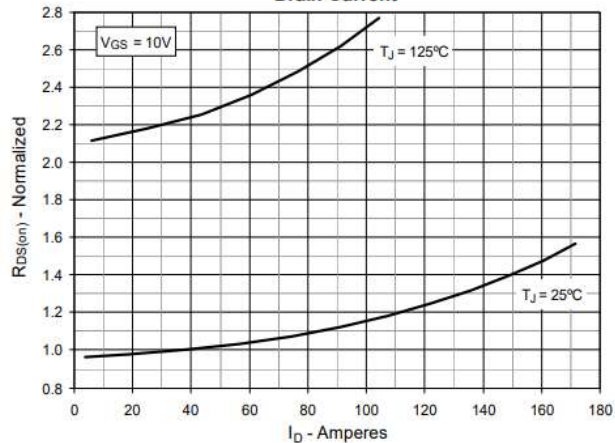
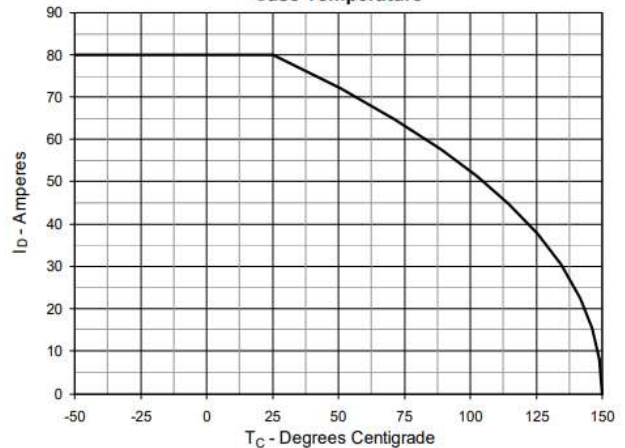


Fig. 6. Maximum Drain Current vs. Case Temperature





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Fig. 7. Input Admittance

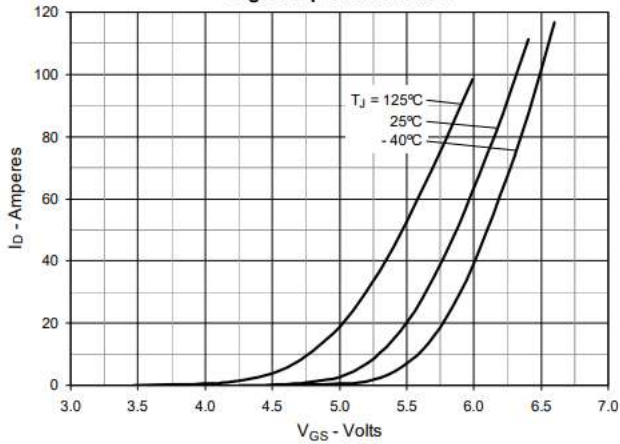


Fig. 8. Transconductance

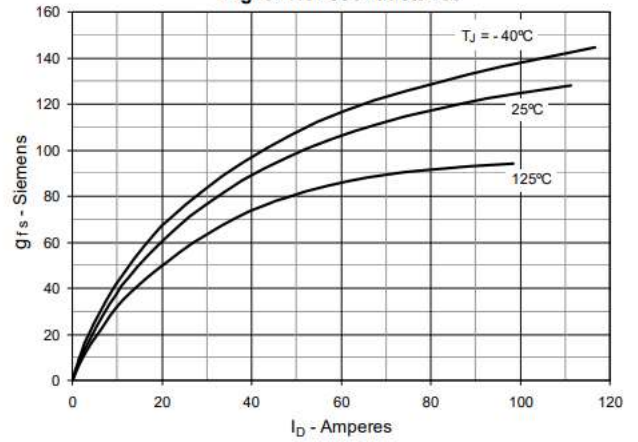


Fig. 9. Forward Voltage Drop of Intrinsic Diode

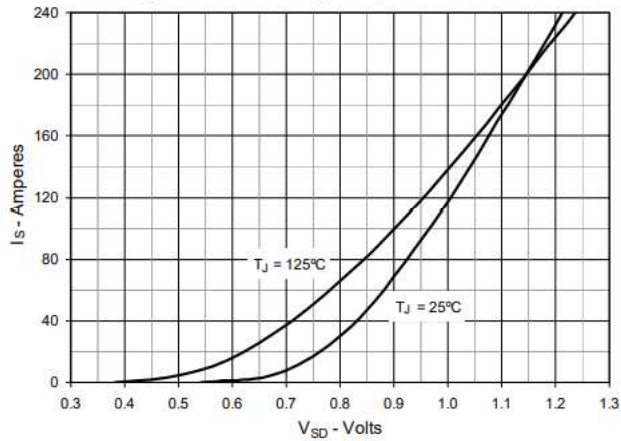


Fig. 10. Gate Charge

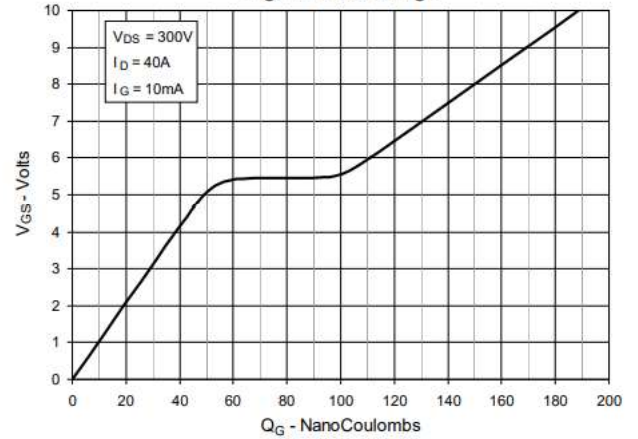


Fig. 11. Capacitance

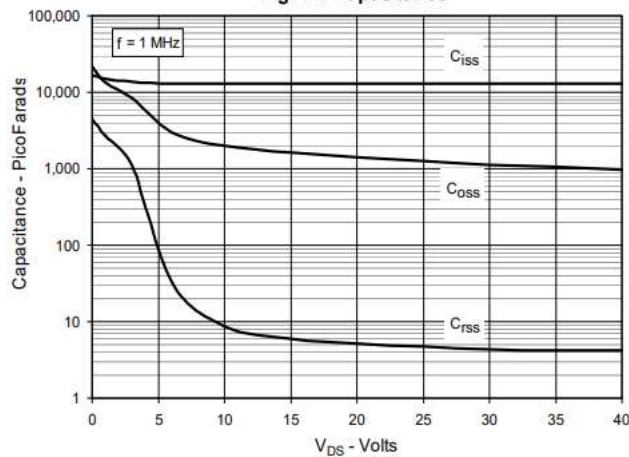
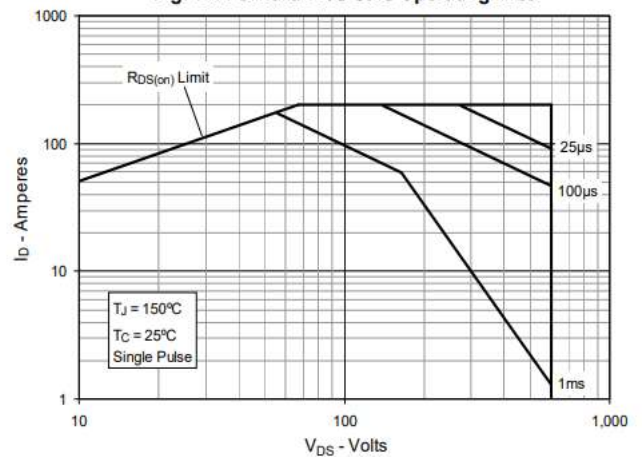


Fig. 12. Forward-Bias Safe Operating Area





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